Abstracts

A New GaAs Power MESFET Structure for Improved Power Capabilities

K. Fricke, V. Krozer and H.L. Hartnagel. "A New GaAs Power MESFET Structure for Improved Power Capabilities." 1989 Transactions on Microwave Theory and Techniques 37.9 (Sep. 1989 [T-MTT] (Special Issue on FET Structures Modeling and Circuit Applications)): 1334-1339.

A new GaAs power MESFET structure incorporating an additional transmission line parallel to the gate allows an increase of the single gate width by a factor of approximately 4. It is experimentally shown that the power capabilities of the new device increase correspondingly if the transmission line is properly terminated. The larger unit gate width results in a significantly higher input resistance.

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